

25A, 50V, 0.047 Ohm, Logic Level, N-Channel Power MOSFET

The RFP25N05L is an N-Channel logic level power MOSFETs are manufactured using the MegaFET process. This process, which uses feature sizes approaching those of LSI integrated circuits gives optimum utilization of silicon, resulting in outstanding performance. The RFP25N05L was designed for use with logic level (5V) driving sources in applications such as programmable controllers, automotive switching, switching regulators, switching converters, motor relay drivers and emitter switches for bipolar transistors. This performance is accomplished through a special gate oxide design which provides full rated conductance at gate biases in the 3V to 5V range, thereby facilitating true on-off power control directly from logic circuit supply voltages.

Formerly developmental type TA09871.

Ordering Information

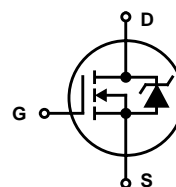
PART NUMBER	PACKAGE	BRAND
RFP25N05L	TO-220AB	RFP25N05L

NOTE: When ordering, include the entire part number.

Features

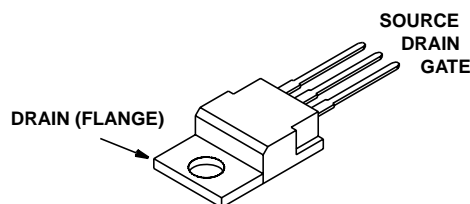
- 25A, 50V
- $r_{DS(ON)} = 0.047\Omega$
- UIS SOA Rating Curve (Single Pulse)
- Design Optimized for 5V Gate Drives
- Can be Driven Directly from CMOS, NMOS, TTL Circuits
- Compatible with Automotive Drive Requirements
- SOA is Power Dissipation Limited
- Nanosecond Switching Speeds
- Linear Transfer Characteristics
- High Input Impedance
- Majority Carrier Device
- Related Literature
 - TB334 "Guidelines for Soldering Surface Mount Components to PC Boards"

Symbol



Packaging

JEDEC TO-220AB



RFP25N05L

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, Unless Otherwise Specified

	RFP25N05L	UNITS
Drain to Source Voltage (Note 1)	50	V
Drain to Gate Voltage ($R_{GS} = 20k\Omega$) (Note 1)	50	V
Continuous Drain Current	25	A
Pulsed Drain Current (Note 3)	65	A
Single Pulse Avalanche Energy Rating (See Figures 4, 15, and 16)	Refer to UIS SOA Curve	
Gate to Source Voltage	± 10	V
Maximum Power Dissipation	60	W
Linear Derating Factor above 25°C	0.48	W/ $^\circ\text{C}$
Operating and Storage Temperature	-55 to 150	$^\circ\text{C}$
Maximum Temperature for Soldering		
Leads at 0.063in (1.6mm) from Case for 10s	300	$^\circ\text{C}$
Package Body for 10s, See Techbrief 334	260	$^\circ\text{C}$

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

1. $T_J = 25^\circ\text{C}$ to 125°C .

Electrical Specifications $T_C = 25^\circ\text{C}$, Unless Otherwise Specified

PARAMETER	SYMBOL	TEST CONDITIONS		MIN	TYP	MAX	UNITS
Drain to Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D = 250μA (Figure 10)		50	-	-	V
Gate to Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 250μA (Figure 9)		1.0	-	2.0	V
Gate to Source Leakage	I _{GSS}	V _{GS} = ±10V, V _{DS} = 0V		-	-	±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 40V, V _{GS} = 0V		-	-	1.0	μA
		T _C = 150°C		-	-	50	μA
Drain to Source On Resistance (Note 2)	r _{DS(ON)}	V _{GS} = 5V, I _D = 25A	(Figures 7, 8)	-	-	0.047	Ω
		V _{GS} = 4V, I _D = 25A		-	-	0.056	Ω
Turn-On Time	t _(ON)	V _{DD} = 25V, I _D =12.5A R _L = 2Ω, R _{GS} = 5Ω (Figures 15, 16)		-	-	60	ns
Turn-On Delay Time	t _{d(ON)}			-	15	-	ns
Rise Time	t _r			-	35	-	ns
Turn-Off Delay Time	t _{d(OFF)}			-	40	-	ns
Fall Time	t _f			-	14	-	ns
Turn-Off Time	t _(OFF)			-	-	100	ns
Total Gate Charge (Gate to Source + Gate to Drain)	Q _{g(TOT)}	V _{GS} = 0 - 10V	V _{DD} = 40V, I _D = 25A, R _L = 1.6Ω (Figures 17, 18)	-	-	80	nC
Gate Charge at 5V	Q _{g(5)}	V _{GS} = 0 - 5V		-	-	45	nC
Threshold Gate Charge	Q _{g(TH)}	V _{GS} = 0 - 1V		-	-	3.0	nC
Thermal Resistance Junction to Case	R _{θJC}			-	-	2.083	°C/W
Thermal Resistance Junction to Ambient	R _{θJA}			-	-	80	°C/W

Source to Drain Diode Specifications

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Source to Drain Diode Voltage	V_{SD}	$I_{SD} = 25A$	-	-	1.5	V
Diode Reverse Recovery Time	t_{rr}	$I_{SD} = 25A$, $dI_{SD}/dt = 100A/\mu s$	-	-	125	ns

NOTES:

2. Pulse Test: Pulse width $\leq 80\mu s$, duty cycle $\leq 2\%$.
3. Repetitive Rating: Pulse width limited by Max junction temperature.

Typical Performance Curves Unless Otherwise Specified

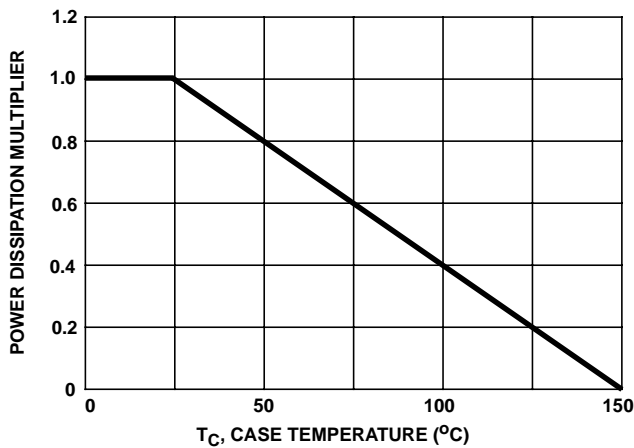


FIGURE 1. NORMALIZED POWER DISSIPATION vs CASE TEMPERATURE

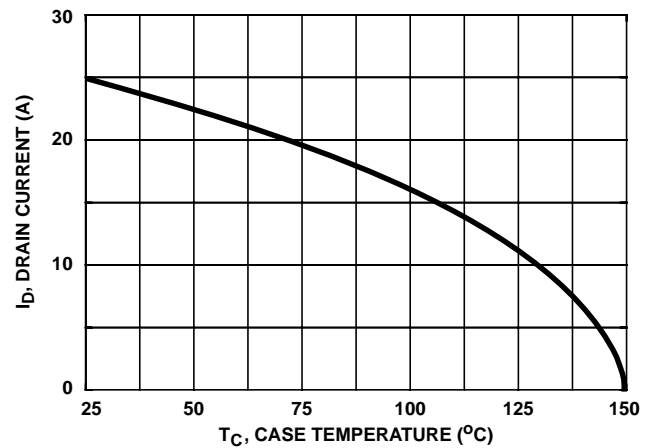


FIGURE 2. MAXIMUM CONTINUOUS DRAIN CURRENT vs CASE TEMPERATURE

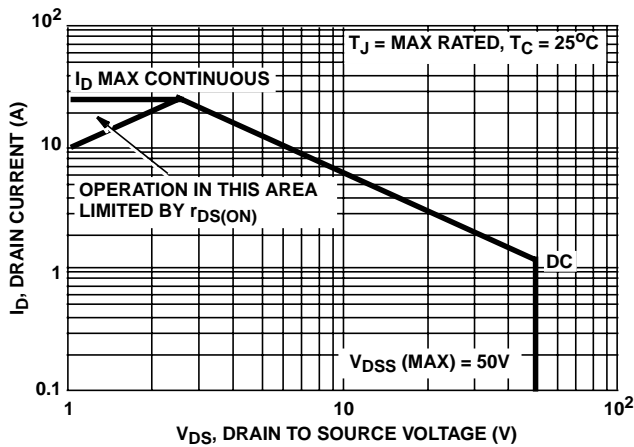


FIGURE 3. FORWARD BIAS SAFE OPERATING AREA

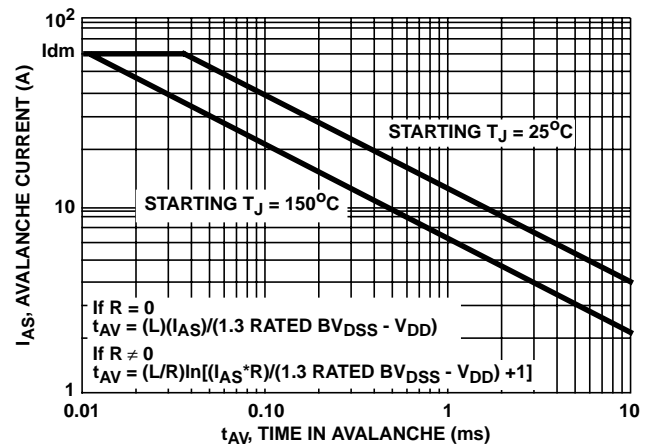


FIGURE 4. UNCLAMPED INDUCTIVE SWITCHING SOA (SINGLE PULSE UIS SOA)

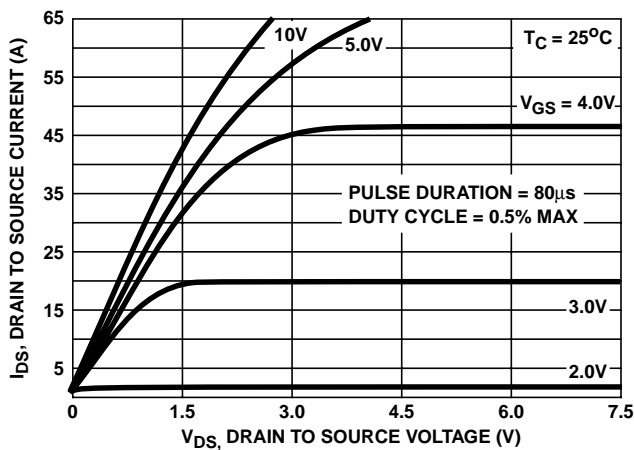


FIGURE 5. SATURATION CHARACTERISTICS

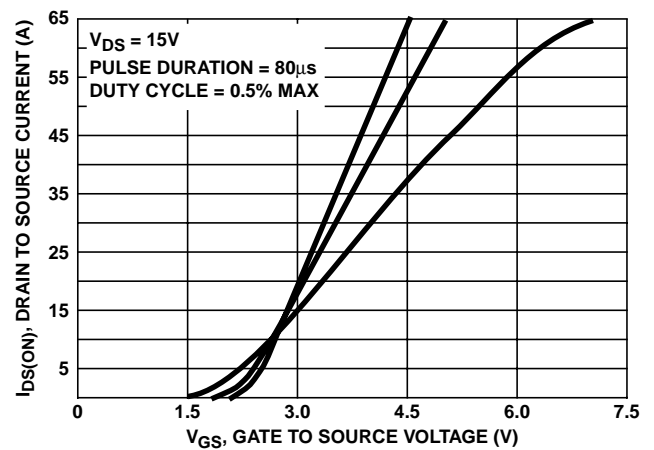


FIGURE 6. TRANSFER CHARACTERISTICS